

**METALLOPORPHYRINS BASED
SEMICONDUCTING THIN FILMS DEPOSITION
AND CHARACTERIZATION FOR
ORGANIC FIELD EFFECT TRANSISTOR**

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UNIVERSITI SAINS MALAYSIA

2017

**METALLOPORPHYRINS BASED SEMICONDUCTING THIN FILMS
DEPOSITION AND CHARACTERIZATION FOR
ORGANIC FIELD EFFECT TRANSISTOR**

by

TAN PI LIN

Thesis submitted in fulfillment of the requirements

for the Degree of

Doctor of Philosophy

February 2017

ACKNOWLEDGEMENTS

I would like to express my deepest gratitude and appreciation to my supervisor and mentors, Professor Ir. Dr Cheong Kuan Yew, Professor Dr. Chow Wen Shyang and Professor Yeap Guan Yeow for their understanding, perseverance, guidance, courage and kindness. They inspired me and their wide knowledge has been of great value to me. Without their advice and knowledge, this research would be impossible.

Thanks to the Dean of School of Material and Mineral Resources Engineering, Professor Dr. Zuhailawati Bt. Hussain for her permission to let me used all the facilities and equipment in the school laboratories in completing my research project. I would like to extend my appreciation to Professor Rupert Schreiner for spending time with me sharing his knowledge regarding the research during my attachment time in Ostbayerische Technische Hochschule Regensburg, Germany. I would like to thanks Professor Zainal Arifin Bin Ahmad, Profesor Dr. Zainal Arifin Bin Mohd. Ishak, Professor Hanafi Bin Ismail, Professor Dr. Azlan Bin Ariffin, Professor Madya Dr. Azura Bt. A. Rashid, Associate Professor Dr. Azhar B. Abu Bakar, Associate Professor Dr. Pung Swee Yong and Dr. Balasauniv, and others for their precious advice on this research work.

In addition, I am in debt with Universiti Sains Malaysia, USM for granting me research fund which are the Research University Postgraduate Research Grant Scheme to support this research project and USM Fellowship for financing me for the first and second year of my research. Thank you USM for the support. Not to forget, Malaysia Toray Science Foundation (MTSF) for providing the funding of this research.

To the school technical staffs especially Mr. Mokhtar, Mr Mohd. Azam, Mr. Azrul, Pn. Haslina, Encik Mohd. Faizal, Encik Abdul Rashid, Encik Muhammad Khairi, En. Helmi, Mr. Zaini, Mr. Zulkarnain, and Mr. Meor, I wish to extend my warmest thanks to all technicians in Ostbayerische Technische Hochschule Regensburg, Germany whom have helped me with my research. They are Ms Maria Komainda, Madam Dagmar Hornik, Madam Hannelore Siegl-Ertl and Madam Daniela Knott.

I owe my loving thanks to my family members especially my parent who is supportive and generous with their encouraging words that help me to keep up with my research work. Without them, I would probably do not have the chance to proceed to this level of academic achievements. To my pals Mr. Teoh Boon Thong, Mr. Teoh Boon Sow, Mr. Alex Phay Chun Keat, Mr. Tan Che Yong, Mr. Hoe, Mr. Tan Teik Cheng, Mr. Lim Tat Wei, Mr. Kang Chew Gan, Mr. Ong Teik Siang, Mr. 王霆遥, Mr. Koek, Mr. Tan Wan Nian, Ms. Khun May, and Mr. Ong. This research work would not be completed without the helping hand from my friends Madam Fong, Dr. Khe Cheng Seong and Mrs. Khe, Dr. Liu Wei Wen, Dr. Tan Kim Seah, Dr. Ann, Dr. Nilar Lwin, Dr. Sam Sun Ting, Dr. Vemal, Dr. Wong Yew Hoong, Dr. Quah Hock Jin, Dr. Lim Way Fong, Mr. Chow Teik Koon, Li Qian, Lim Zhe Xi, Azhar, Lian Na, Ratna, Shazlin and my fellow research colleagues. Therefore, I again would like to express my gratitude to them all who have made this thesis possible.

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LIST ABBREVIATIONS

| | |
|-----------|---|
| OFET | Organic Field effect Transistor |
| OTFT | Organic Thin Film Transistor |
| MOSFET | Metal-oxide-semiconductor field-effect transistor |
| OEP | Octaethyl-21H, 23H-Porphine |
| OEP-Cu | Octaethyl-21H, 23H-Porphine Copper (II) |
| OEP-Ni | Octaethyl-21H, 23H-Porphine Nickel (II) |
| OEP-Zn | Octaethyl-21H, 23H-Porphine Zinc (II) |
| Proto-Zn | Protoporphyrin IX Zinc (II) |
| Proto-Co | Protoporphyrin IX Cobalt Chloride |
| AOEP | Annealed Octaethyl-21H, 23H-Porphine |
| AOEP-Cu | Annealed Octaethyl-21H, 23H-Porphine Copper (II) |
| AOEP-Ni | Annealed Octaethyl-21H, 23H-Porphine Nickel (II) |
| AOEP-Zn | Annealed Octaethyl-21H, 23H-Porphine Zinc (II) |
| AProto-Zn | Annealed Protoporphyrin IX Zinc (II) |
| AProto-Co | Annealed Protoporphyrin IX Cobalt Chloride |
| BCB | Benzocyclobutene |
| ITO | Indium Tin Oxide |
| i.e | Id est /that is |
| vs | Versus |
| Ag | Silver |
| Au | Gold |

| | |
|------------------|-------------------------------------|
| Cu | Copper |
| Al | Aluminium |
| Pt | Platinum |
| Ge | Germanium |
| Si | Silicon |
| GaAs | Gallium arsenide |
| GaP | Gallium phosphide |
| HOMO | Highest occupied molecular orbital |
| LUMO | Lowest unoccupied molecular orbital |
| TCNQ | Tetracyanoquinodimethane |
| P3HT | Poly(3-hexylthiophene) |
| PPV | Poly(p-phenylenevinylene) |
| PFO | Polyfluorene |
| P3AT | Poly(3-alkylthiophene) |
| CuPc | Cu-phthalocyanine |
| C ₆₀ | Fullerene |
| Alq ₃ | tris(8-hydroxyquinolinato)aluminium |
| PC | Polycarbonate |
| PP | Polypropylene |
| PET | Polyethylene terephthalate |
| PVDF | Polyvinylidene fluoride |
| PEN | Polyethylene naphthalate |
| PPS | Polyphenylene sulphide |